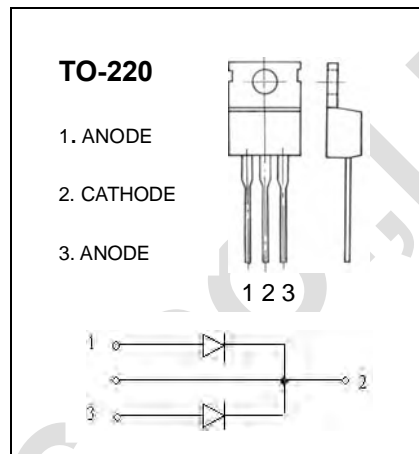


MBR2030CT-MBR2060CT

SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Characteristic	Symbol	MBR 2030	MBR 2035	MBR 2040	MBR 2045	MBR 2050	MBR 2060	Unit
Peak Repetitive Reverse Voltage	V_{RRM}							
Working Peak Reverse Voltage	V_{RWM}	30	35	40	45	50	60	V
DC Blocking Voltage	V_R							
PMS Reverse Voltage	$V_{R(RMS)}$	21	24.5	28	31.5	35	42	V
Average Rectified Output Current (Note 1) @ T _c =125°C	I_o	20						A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	150						A
Forward Voltage Drop @ I _F =20A, T _c =25°C @ I _F =20A, T _c =125°C @ I _F =10A, T _c =25°C @ I _F =10A, T _c =125°C	V_{FM}		0.84 0.72 0.70 0.57			0.95 0.85 0.80 0.70		V
Peak Reverse Current @ T _c = 25°C at Rated DC Blocking Voltage @ T _c =125°C	I_{RM}				0.1 15			mA
Typical Junction Capacitance (Note 2)	C_j				650			pF
Operating and Storage Temperature Range	T _j , T _{STG}				-65 to +150			°C

Notes: 1. Thermal resistance junction to case mounted heat sink.
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.